2SC2733

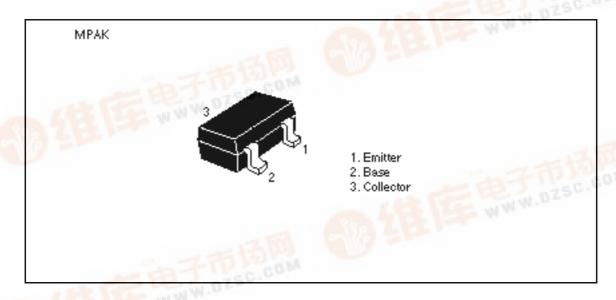
Silicon NPN Epitaxial

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Application

WWW.DZSG VHF frequency converter

Outline





2SC2733

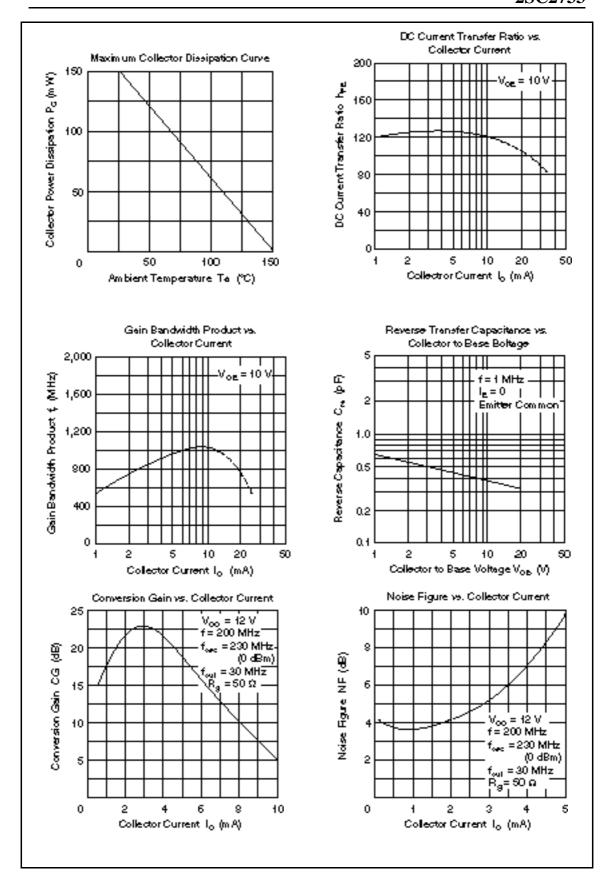
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

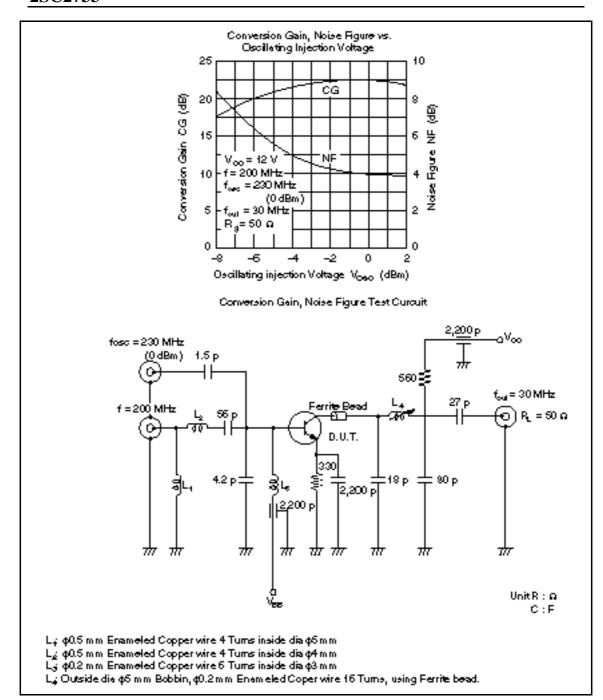
Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	30	V
Collector to emitter voltage	V _{CEO}	20	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I _c	50	mA
Collector power dissipation	P _c	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	_	_	V	$I_{\rm C} = 10 \ \mu A, \ I_{\rm E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	20	_	_	V	$I_{\rm C}$ = 1 mA, $R_{\rm BE}$ =
Emitter to base breakdown voltage	$V_{(BR)EBO}$	3	_	_	V	$I_E = 10 \ \mu A, \ I_E = 0$
Collector cutoff current	I _{CBO}	_	_	0.5	μΑ	$V_{CB} = 10 \text{ V}, I_{C} = 0$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	1.0	V	$I_{\rm C}$ = 20 mA, $I_{\rm B}$ = 4 mA
DC current transfer ratio	h _{FE}	60	120	_		$V_{CE} = 10 \text{ V}, I_{C} = 10 \text{ mA}$
Gain bandwidth product	f _T	600	1000	_	MHz	$V_{CE} = 10 \text{ V}, I_{C} = 10 \text{ mA}$
Collector output capacitance	Cob	_	0.35	0.65	pF	$V_{CB} = 10 \text{ V}$, Emitter ground, $f = 1 \text{ MHz}$
Conversion gain	CG	_	21	_	dB	$\begin{split} &V_{\text{CC}} = 12 \text{ V}, \text{ I}_{\text{C}} = 2 \text{ mA}, \\ &f = 200 \text{ MHz}, \\ &f_{\text{OSC}} = 230 \text{ MHz (0dBm)}, \\ &f_{\text{out}} = 30 \text{ MHz} \end{split}$
Noise figure	NF	_	4.0	_	dB	$V_{CC} = 12 \text{ V}, I_{C} = 2 \text{ mA},$ f = 200 MHz, $f_{OSC} = 230 \text{ MHz (0dBm)},$ $f_{out} = 30 \text{ MHz}$

Note: Marking is "HC".





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